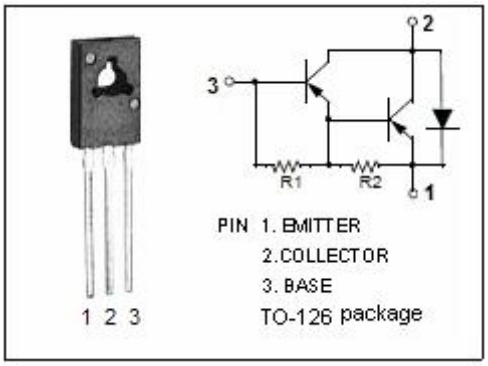
isc Silicon PNP Darlington Power Transistor BD262



DESCRIPTION

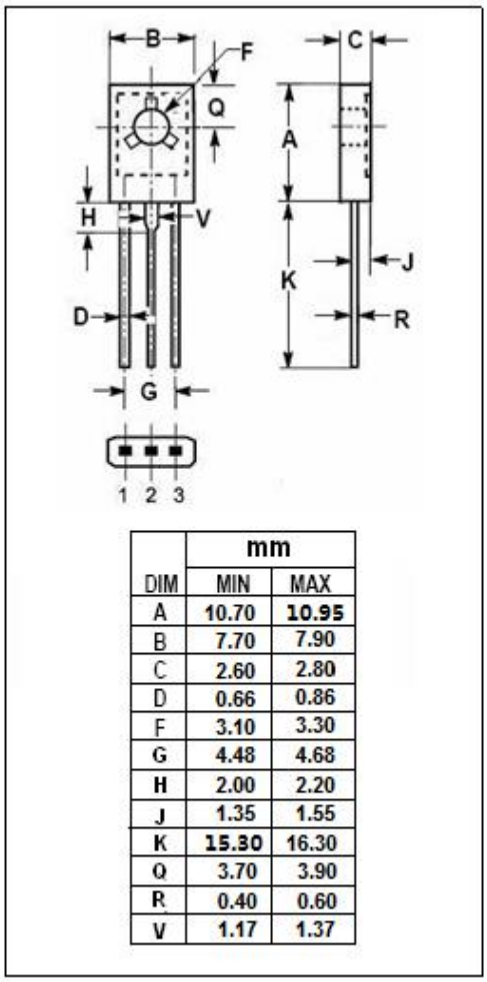
- Collector–Emitter Sustaining Voltage—
  : $V_{CEO(SUS)}$ = -60V(Min.)
- DC Current Gain—
  : h_{FE} = 750(Min) @ I_C= -2A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-6	A
I_{CM}	Collector Current-Peak	-10	A
I_B	Base Current	-0.1	A
P_C	Collector Power Dissipation T_C=25℃	36	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -10mA; I_B= 0	-60		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= -3A ,I_B= -12mA		-2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= -5A ,I_B= -20mA		-3.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -4A; V_{CE}= -3V		-2.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -60V; I_B= 0		-0.2	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -60V; I_E= 0		-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-2.0	mA
h_{FE-1}	DC Current Gain	I_C= -0.5A ; V_{CE}= -3V	750		
h_{FE-2}	DC Current Gain	I_C= -2A ; V_{CE}= -3V	750	15000	
h_{FE-3}	DC Current Gain	I_C= -4A ; V_{CE}= -3V	100		
f_T	Current Gain-Bandwidth Product	I_C= 0.5A ; V_{CE}= 10V;f=1.0MHz	7		MHz